Crystal Growth, Structural and Electrical Properties of Rubidium and Cesium Vanadium Oxide Bronzes

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Crystals of the following compounds were grown by cathodic reduction of $C_{S}-V^{5+}-O$ or $Rb-V^{5+}-O$ metls: $C_{S_0,3}V_2O_5$ (A), $C_{S_2}V_5O_{13}$ (B), $C_SV_2O_5$ (C), $Rb_{0,4}V_2O_5$ (D), $Rb_{0,37}V_2O_{-4.8}$ (E) (a new orthorhombic compound) and $Rb_{2-x}V_{3+2x}O_{8+2x}$ (F). The crystal symmetry and cell parameters of the Rb compounds (which were known for F only) were determined, as well as those of $Rb_{0,3}V_2O_5$, which has the structure of A. Magnetic susceptibility and ESR measurements confirm the intermediate valence in E. A, C, and E are semiconductors with activation energies in the range 0.07-0.2 eV. $Cs_{0,3}V_2O_5$ (A), in which V⁴⁺ and V⁵⁺ do not occupy distinct crystallographic sites, has the highest electrical conductivity. © 1987 Academic Press, Inc.

Introduction

Vanadium oxide bronzes (VOB's), i.e., ternary vanadium oxides containing vanadium with an oxidation state between +4and +5, are known to exist with various univalent or divalent metal cations (1, 2). Those formed by rubidium and cesium have been much less studied than their lighter alkali metal or IB metal counterparts (1, 2). Fotiev et al. (3-5) reported a number of M_2 V_2O_5 compounds with M = Rb or Cs, but did not publish any structural data or physical properties; the nomenclature used in their papers is rather confusing (the compound later identified as $Cs_2V_5O_{13}$, for instance, was named "ζ-phase" (3), " ν -phase" (4), and " σ -phase" (5), successively). The only well-characterized rubidium compound is $Rb_{2-x}V_{3+2x}O_{8+2x}$ (6), which is isostructural of the potassium " ϕ -VOB" (7, 8). Cesium VOB's have been better characterized, because single crystals were prepared by either electrolysis (Reid and Watts (9), two compounds) or a flux method under controlled oxygen pressure (Forslund and Jelinski (10), four compounds). The structures of these four cesium VOB's have been determined (11, 12), and their electrical and magnetic properties have been recently reported (13).

These heavy alkali metal VOB's are interesting because they adopt structures differing from VOB's containing light univalent cations, which form a fairly homogeneous family (1). In particular, the very common β -VOB structure (14), which can accommodate various cations with octahedral ionic radii (15) up to ~140 pm (Ba²⁺, K⁺), does not occur for Rb⁺ and Cs⁺ (ionic radius 152 and 167 pm, respectively). Cesium VOB's crystallize with either a layer or channel structure. The former are insulating, while the latter are semiconductors with activation energies of conductivity near 50 meV and unexplained slope changes in their log σ vs T^{-1} curves (13).

Chemically, Rb- and Cs-VOB's do not resemble the typical tungsten oxide bronzes, which were early noted for their remarkable chemical inertness. In a study of electrolytic crystal growth of potassium VOB's, Babenko et al. (16) were able to wash the bronze crystals in a 50% NaOH solution. On the contary, Fotiev et al. (3)noted that Rb- and Cs-VOB's are readily decomposed in alkalies, as well as in acids. This property, which is confirmed by the present work, makes difficult the recovery and washing of crystals. For flux growth, Forslund and Jelinski had to build a movable suction tube to pick up crystals before melt cooling (10).

The present paper reports a systematic investigation of single-crystal synthesis of Rb- and Cs-VOB's by electrolysis, the structural and ESR characterization of Rb-VOB's, and electrical conductivity measurements on single crystals. Preliminary results of crystal growth have been discussed in Ref. (17). A new orthorhombic structure, which is not known in either the potassium or cesium VOB's system, was found in the Rb-V-O system and obtained as single crystals up to 3 mm long.

Experimental

The electrolytic arrangement used in this work has been described previously (17, 18). Starting materials were reagent grade Rb_2CO_3 , Cs_2CO_3 , and V_2O_5 (Alfa-Ventron or Prolabo), heated in high-purity alumina crucibles (McDanel Co.). In a typical run, the sample charge was first intimately mixed and heated slowly to 400°C in air, allowing the carbonates to decompose. The temperature was then increased to the melting point and melting was checked visually. The temperature was finally stabilized at 20-30°C above the melting point, and the cathode was lowered down to the surface of the melt. The electrolysis was carried out for several days with a stabilized current (usually <20 mA). Preliminary attempts carried out in argon atmosphere (in the rubidium system) gave results similar to those carried out in air. Detailed experimental conditions are given in Table I. At the end of the process, the cathode was raised above the melt before cooling. Recovery of the crystals was difficult because the cathode tip frequently carried a group of crystals imbedded in solidified vanadate. The vanadate block had to be broken and washed out with water or dilute ammonia. As noted by Fotiev et al. (3), the use of acids, even dilute, resulted in the loss of the crystals.

Crystals were identified by X-ray diffraction (precession camera) and electron diffraction (PHILIPS 400T electron microscope). Accurate cell parameters were obtained by a least-squares refinement from room-temperature powder X-ray diffraction in a Guinier camera (FeK α radiation, internal silicon standard). The composition of crystals of rubidium VOB's was determined by microprobe analysis of Rb and V, using pure vanadium as a primary standard and $Rb_2V_3O_8$ as a secondary standard. An average of 25 countings was made with the electron beam scanning across the surface of cut and polished samples. The standard deviation was in each case within 2%, with the exception of the Rb determination in the rubidium " ν " compound, for which the scattering reached 5%.

Magnetic susceptibilities were measured in the range 4-300 K using a Faraday balance with a 660 kA/m field. The observed susceptibilities were corrected for diamagnetism (19) and for V_2O_5 temperature-independent paramagnetism (see below). ESR spectra of the new rubidium phase were recorded down to 8 K at X-band frequencies with a Thompson THN 251

Run	Melt composition (mole% M ₂ CO ₃)	Temp. (°C)	l (mA)	Time (Days)	Crystals recovered	Identification
			(A) C	s-V-O sys	stem	
1, 2	12-13	600	25-50	8-14	$(V_2O_5 + Pt \text{ dendrites})$	
3		570	9.0	7	Dark needles	Cs _{0.3} V ₂ O ₅ (12)
	15.0				2–3 mm long	
4	30.0	500	10.1	11	Black plates $2 \times 2 \times 0.2$ mm	$Cs_2V_5O_{1.3}$ (9, 12)
5	37.0	460	7.0	12	Black plates $2 \times 2 \times 0.2$ mm	CsV ₂ O ₅ (9, 11)
			(B) I	Rb-V-O S	ystem	
6		600	20.4	5	Yellow needles	V ₂ O ₅
7	9.8 ~20.7	535	10.0	5	Brown blocks (cathode) $5 \times 3 \times 2 \text{ mm}^a$	" <i>v</i> '-VOB" mono- clinic (22)
					+ black needles up to 3 mm long ^b	New orthorhom- bic phase
8		510	15.0	8	As in run 7	•
9	21.9 22.0	~500	60.0	8	Black blocks or plates	"ν'-VOB"
10, 11	27.0 - 29.2	490-540	10-17	6-10	As in run 9	"ν'-VOB"
12, 13	40.0	500	6.6	10	Brown blocks $5 \times 3 \times 3$ mm	~Rb ₂ V ₃ O ₈ (''ф-VOB'') (б)

TABLE I

EXPERIMENTAL CONDITIONS AND RESULTS OF ELECTROLYTICAL CRYSTAL GROWTH

^a Cleave easily as thin platelets.

^b Recovered from solidified melt surface or crucible walls.

spectrometer calibrated with P-doped silicon (g = 2.0038).

Electrical resistivities were determined in the temperature range 77-300 K using a four-probe arrangement. The voltage drop across the samples was measured by a Keithley 610 electrometer. Electrical contacts were made of evporated or ultrasonically applied indium. Dimensions of the samples were measured with a microscope using a calibrated grid. Uncertainties about the absolute values of the resistivity were estimated to be about 20% due to the irregular shape of the samples; the error in the relative values and in the slope of the temperature dependence was much smaller.

Results and Discussion

1. Crystal Growth and Characterization

The conditions and results of electrochemical synthesis are summarized in Table I. Three rubidium phases and three cesium phases were obtained, depending on the composition of the melt.

1.1. Cesium compounds. In the Cs-V-O system, electrolysis yielded crystals of Cs₂ V_5O_{13} and CsV₂O₅ previously obtained by Reid and Watts (9). The alkali contents required, however, were lower than those reported by Reid and Watts. A decrease in this content below 22 mole% leads to a markedly higher liquidus temperature (20,



FIG. 1. The relationship between melt and cathodic deposit composition in the Cs-V-O system.

21), making more difficult the synthesis of the oxide bronzes, which have limited thermal stability. Crystals of $C_{S_{0,3}}V_2O_5$ were grown in this composition range at 570°C. There is an obvious relationship between the Cs/V ratio in the crystals deposited and the composition of the melt (see Fig. 1). However, further attempts at low alkali content, which required temperatures in excess of 600°C, produced no oxide bronze crystals; platinum dendrites formed on the cathode in several runs, indicating partial dissolution of the platinum anode in the melt.

 $Cs_2V_5O_{13}$ and CsV_2O_5 grow as thin plates, whereas $Cs_{0.3}V_2O_5$ gives acicular crystals. The habits and structures of these compounds confirm the results of Forslund *et al.* (12, 13). $Cs_{0.35}V_3O_7$, which was prepared by solid state reaction at 500-600°C (10), could not be obtained electrochemically, probably because of the high temperatures required to melt the mixtures with low Cs/ V ratios.

1.2. Rubidium compounds. Although Fotiev and co-workers (3-5) reported no less

than six rubidium VOB's (characterized only by unindexed powder X-ray diffraction patterns), only three compounds were found in the present work. The critical temperature for bronze deposition on the cathode seems to be about 600°C. A quite surprising result was the reproducible formation of two oxide bronzes simultaneously in melts with ~21 mole% Rb₂CO₃ (see Table I). Cathodic reduction yielded $Rb_{\sim 0.4}V_2O_5$ platelets, while crystals several millimeters long of a new compound grew on the crucible walls or at the surface of the solidified melt. Rb_{~0.4}V₂O₅ was formed from a rather wide range of melt compositions (20 to 27 mole% Rb) and was found to exist with a range of compositions: the crystals grown from a 27 mole% melt have a larger Rb content and a smaller O/V ratio (see Table II). At higher rubidium concentrations, the known compound $Rb_2V_3O_8$ (actually slightly nonstoichiometric) grew. It has a typically layered morphology and cleaves easily into very thin plates.

The results of chemical analysis and structural characterization are given in Ta-

Run	Composition	Phase	Crystal system	Space group	Cell parameters (pm)
8	Rb _{0.365(6)} V ₂ O _{4.8(1)}	ν'	Monoclinic	C2/m	a = 1163(4)
9	Rb _{0.38(2)} V ₂ O _{4.8(2)}				b = 366.4(8)
10	$Rb_{0,40(2)}V_2O_{4,6(3)}$				c = 975(3) B = 101.2(5)
7	Rb _{0.383(7)} V ₂ O _{4.65(15)}	New	Orthorhombic	C222 or	a = 1522.1(5)
8	Rb _{0.375(4)} V ₂ O _{4.99(8)}			Cmm2 or Cmmm	b = 361.8(1) c = 1499.7(4)
12	Rb1 88(2) V3 24O8 24	ø	Tetragonal	P4/*b*	a = 892.0(1)
13	Rb _{1.85(4)} V _{3.30} O _{8.30}	,	5		c = 553.9(1)
	$\frac{\text{Rb}_{0.3}\text{V}_2\text{O}_5}{\text{or }\text{Rb}\text{V}_6\text{O}_{15}{}^a}$	Cs _{0.3} V ₃ O ₅	Hexagonal	P6 ₃ /m	a = 1415.1(6) c = 358.6(1)

IABLE II	TABLE	П
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CHEMICAL COMPOSITION AND STRUCTURAL CHARACTERIZATION OF Rb-Vanadium Oxide Bronzes

^a Not found in this work; cell parameters obtained by indexing X-ray data from Ref. (4) in the $Cs_{0.3}V_2O_5$ cell.

ble II. The two compounds obtained simultaneously in Runs 7 and 8 have very close Rb/V ratios, but they differ by their crystal habit and unit cell as shown by powder and single-crystal X-ray diffraction. Both, however, exhibit a short *b* parameter (~365 pm) which is typical of structures derived from V_2O_5 . This parameter represents the double of a VO₅ square-pyramid height in V_2O_5 ; it is found in the oxides V_nO_{2n+1} and in many VOB's (22) (but in none of the cesium VOB's).

Monoclinic $Rb_{-0.4}V_2O_5$ appears to be the rubidium homolog of the " ν' phase" K_{~0.6} V_2O_5 (23). Its structure is not known; precession photographs show that all crystals obtained are badly twinned. The $Rb_{\sim0.4}V_2$ O_5 unit cell (Table II) is very similar to that of Ca_{0.6}V₂O₅ (24), which contains zig-zag chains of edge-sharing distorted VO₅ pyramids (described in Ref. (24) as distorted octahedra). Such a framework, in which there are no specific sites for V⁴⁺ ions, is characteristic of VOB's (22).

The new compound is C-centered orthorhombic. Its unit cell (Table II) does not present any simple relationship with that of other known VOB's. Because of twinning, a single-crystal structural study could not been carried out. The unit cell was confirmed by electron diffraction. The needle axis is the shortest cell axis b. Indexed powder patterns of $Rb_{\sim 0.4}V_2O_5$ and $Rb_{0.37}V_2O_{4.8}$ are given in Table III.

The third rubidium VOB obtained here is the tetragonal " ϕ -phase," which is slightly nonstoichiometric ($Rb_{2-x}V_{3+2x}O_{8+2x}$ with x = 0.13) and grew as plates perpendicular to c. The previously reported compound $Rb_{0.3}$ V_2O_5 (or RbV_6O_{15}) (3, 4) was not found in the present study, possibly because it would require a melt composition with too high liquidus temperature. An examination of its powder pattern (JCPDS n° 30-1098) reveals a striking resemblance to that of the hexagonal cesium VOB Cs_{0.3}V₂O₅ and correspnds to the cell parameters given in Table II. The few powder diffraction lines previously attributed to two compounds Rb_xV_2 O_5 with $x \sim 0.4$ (3-5) are mostly included in the powder patterns of $Rb_{0.37}V_2O_{4.8}$ and $Rb_{\sim 0.4}V_2O_5$ (see Table III). Note that previous synthesis in the Rb-V-O system was carried out by solid state reactions (3-6).

As discussed by Nygren *et al.* (13), it is difficult to reach homogeneous phases by this technique.

2. Physical Properties

2.1. Magnetic properties. The magnetic susceptibilities of the tetragonal and orthorhombic rubidium VOB's have been measured. The former follows a Curie-Weiss law down to 10 K with $\theta = -16$ K and C = 0.590 emu K/mole, corresponding to a magnetic moment of 1.718 Bohr magnetons for V⁴⁺ in Rb_{1.88}V_{3.24}O_{8.24} (theoretical spin-only value: 1.732). This behavior is very similar to that of the potassium homolog (25). On the contrary, the variation of the reciprocal susceptibility of the new orthorhombic bronze Rb_{0.37}V₂O_{4.8} (which could be measured up to 180 K only) exhibits a strong curvature towards the T axis below ~90 K (see Fig. 2). No meaninful magnetic moment was extracted from the data. It was checked that the curvature of

TABLE III

X-RAY POWDER DIFFRACTION PATTERNS OF RUBIDIUM VANADIUM OXIDE BRONZES

$d_{\rm obs}$	d_{calcd}		_
(pm)	(pm)	hkl	I _{obs}
(a) R	b _{~0.4} V ₂ O ₅	(" <i>v</i> '-phase	e'')
345ª	348.5	110	60
336	336.2	202	100
331ª	333.8	111	<10
323.7ª	321.5	111	20
306.9	304.5	$\overline{2}$ 0 3	40
284.4	284.7	400	40
264.0ª	263.5	310	60
259.7	259.7	401	40
226.6	226.4	402	<10
202.8	203.0	114	40
195.9	195.8	511	10
193.0	193.1	$\bar{2}$ 0 5	40
184.5	183.9	511	60
180.1	179.8	021	40
	179.7	601	

TABLE III—Continued

IA.		Commue	<i>.</i>
dobs	$d_{\rm calcd}$		
(pm)	(pm)	hkl	I _{obs}
(b) R	.b _{0.37} V ₂ O _{4.8}	(new pha	se)
760	761.0	200	20
682	678.7	201	20
535°	534.1	202	40
500°	499.9	003	<10
417.6 ^b	417.8	203	60
374.9	374.9	004	20
368.6*	368.8	401	60
342.8	342.7	111	100
339.1 ^b	339.3	402	100
336.4	336.3	204	40
318.6	318.6	112	60
302.9 ^b	302.8	403	60
299.8	299.9	005	60
294.5	294.6	310	40
288.9 ^b	289.0	311	60
287.9	287.8	113	60
279.2 ^ø	279.1	205	40
274.4	274.2	312	40
267.4 ^b	267.1	404	20
256.5	256.6	114	60
253.8 ^b	253.8	313	40
237.5*	237.5	206	40
233.05	232.9	510	10
230.1	230.2	511	10
228.1	228.3	115	40
226.1	226.2	603	20
211.2	211.1	513	10
210.0	210.1	604	40
209.2	208.9	406	40
203.7	203.8	116	40
198.2	197.9	514	20
190.5	190.6	316	40
186.4	186.37	710	10
185.05	194.95	711	10
183.95	183.97	515	20
180.9	180.90	020	80
169.9	170.10	023	10
150 4	169.67	804	
157.6	159.63	422	20
137.8	15/.04	21/	20
154.9	154.91	023	20
152.6	152.64	409	20

^a Lines of Volkov's " δ " phase (4); also at d = 241,182.6.

^b Lines of Fotiev's " δ "-phase (3); also at d = 560, 306, 270, 249,240 (all very weak).



FIG. 2. Low-temperature magnetic susceptibility of Rb_{0.37}V₂O_{4.8} (plotted as χ^{-1} vs T).

 $\chi^{-1}(T)$ is not due to the contribution of V₂ O₅, which is a temperature-independent paramagnet above ~80 K, but often exhibits impurity paramagnetism at low temperature (26), as shown in "Prolabo" V₂O₅ (see Fig. 2, inset). The temperature dependence of Rb_{0.37}V₂O_{4.8} reverse susceptibility (after correction for the V₂O₅ contribution) probably indicates short-range antiferromagnetic interactions.

ESR spectra were recorded on bunches of twinned acicular crystals with a common needle axis b at variable (H, b) angle. A single resonance line is observed (Fig. 3) with $g = 1.982 \pm 0.002$ (b||H) and g = 1.933 ± 0.005 $(b \perp H)$. These g-values are typical of oxide lattices with V⁴⁺ centers in an axially distorted crystal field (26–28). The peak-to-peak linewidth ΔH shows a broad plateau in the range 8–25 K (~42 G), then increases with temperature (82.5 G at 80.1 K). No low-temperature decrease of ΔH with T, such as that occurring in copper VOB's (and ascribed to motional narrowing by hopping $3d^1$ electrons (26)), was observed. The lack of hyperfine structure in $Rb_{0.37}V_2O_{4.8}$ indicates that the hopping frequency of the $3d^1$ electron is larger than the hyperfine coupling constant (in frequency units).

2.2. Electrical properties. The resistivities of crystals of five VOB's were measured (crystals of the ν' -phase were too brittle for the attachment of contacts). For $Cs_{0.3}V_2O_5$, contacts deposited by evaporation-condensation of indium were used and particular care was given to the acquisition of data points in the range 90-100 K, where a semiconductor-semiconductor transition with a jump in resistance by a factor ~ 2 was reported (13). There is a slight curvature in log $\sigma = f(T^{-1})$ in that temperature range (see Fig. 4a), but no transition was found in any of the three crystals examined (measurements were made parallel to the c axis). Activation energies are comparable with those reported by Nygren *et al.* (13)(see Table IV). It should be noted that the magnetic susceptibility curve of $Cs_{0.3}V_2O_5$ exhibits no anomaly near 97 K (13), and that similar unexplained jumps in σ at 98– 115 K were found on other compounds by Nygren et al. (Fig. 6 in Ref. (13)), which may indicate some instrumental effect in their measurements. The fairly good electrical conductivity of $Cs_{0.3}V_2O_5$ and its low activation energy (which is of the same order of magnitude as those of semiconduct-



FIG. 3. ESR spectrum of polycrystalline $Rb_{0.37}V_2$ $O_{4.8}.$

ing sodium VOB's (1)) are consistent with its structure, which contains V^{4+} ions statistically distributed among the vanadium sites. This feature is characteristic of an oxide bronze, and favors conduction by smallpolaron hopping through the framework vanadium sites (27, 29).

The new orthorhombic compound $Rb_{0.37}$ V₂O_{4.8}, which exhibits comparable structural features (see Section 1.2), is a fairly

good electrical conductor, with a small activation energy (see Fig. 4b). The alkali metal-richer compounds, however, are much poorer conductors (Table IV). The temperature variation of the resistivity could be measured for $C_{S}V_{2}O_{5}$ only (see Fig. 4c), while $C_{S_{2}}V_{5}O_{13}$ and the rubidium ϕ -phase can be practically regarded as insulators. These three compounds share similar structural features, departing from typi-



FIG. 4. Electrical resistivity of bronze phases versus reciprocal temperature: (a) $Cs_{0.3}V_2O_5$ (two single crystals, measurement along the *c* axis); (b) $Rb_{0.37}V_2O_{4.8}$ (block of twinned crystals, measurement along the *b* axis); (c) CsV_2O_5 (single crystal).

	Sample origin	Approximate RT conductivity $(\Omega^{-1} \text{ cm}^{-1})$	Activation conductivi	Shortest V. V.	
Formula			100-300 K	80–95 K	distance (pm)
$Cs_{0.3}V_2O_5$	Ref. (13)	~5	62	53	304 <i>ª</i>
	Run 3	~2	73	55	
$Rb_{0.38}V_2O_{4.8}$	Run 8	0.5	75		?
CsV ₂ O ₅	Run 5	5 10-5	190		307 <i>^b</i>
					335°
$Rb_{1.88}V_{3.2}O_{8.2}$	Run 12	<10 ⁻⁹			348°
$Cs_2V_5O_{13}$	Run 4	<10 ⁻⁹			348°

TABLE IV					
ELECTRICAL PROPERTIES OF Rb AND Cs	VOB's				

^a Sites statistically occupied by V⁴⁺ or V⁵⁺.

^b Distance $V^{4+} - V^{4+}$ (isolated pairs).

^c Distance V⁴⁺-V⁵⁺.

cal oxide-bronze character, which can explain their insulating character. They are built up of layers containing V^{4+} and V^{5+} on distinct crystallographic sites with different oxygen coordination (square pyramidal for V^{4+} , tetrahedral for V^{5+} (8, 12)). Moreover, in each of these compounds, the single V⁴⁺ atom is more strongly bonded to one oxygen atom, with one V^{4+} -O distance 158-160 pm, typical of the vanadyl ion VO²⁺. Thus they can be written as Cs $(V^{IV}O)(V^{V}O_4)$, $Cs_2(V^{IV}O)(V^{V}O_3)_4$, and Rb_2 $(V^{IV}O)(V_2^VO_7)$, and should be considered as ionic mixed oxides rather than oxide bronzes. (The $M_2V_3O_8$ structure is actually that of the ionic mineral fresnoite, Ba₂(TiO) (Si_2O_7) (30)). No electronic conduction is to be expected in this case; hopping between V^{4+} and V^{5+} sites is hampered by the important differences in size and environment geometry of the V^{4+} and V^{5+} sites and by prohibitively long V-V distances, except in $C_{s}V_{2}O_{5}$ (see Table IV).

Conclusion

Crystals of three rubidium and three cesium vanadium oxide bronzes were prepared. This proves the usefulness of molten salt electrolysis in the synthesis of interme-

diate-valence compounds, as an alternative to chemical reactions under controlled oxygen pressure. The crystallographic cells of four rubidium VOB's were determined. Two of these (the ν' and ϕ -phases) are isostructural with known potassium compounds; one has an orthorhombic cell which is new among VOB's, while the previously reported $Rb_{0.3}V_2O_5$ (or RbV_6O_{15}) is found isostructural with a cesium compound. In the Cs-V-O system, this study fully confirms the results of Waltersson and Forslund (12). Electrical measurements on $Cs_{0.3}V_2O_5$, however, do not support a previously reported jump in conductivity, which was attributed to a semiconductor-semiconductor transition (13). Rb- and Cs-VOB's are interesting examples of mixedvalence oxides with widely different electrical properties connected to localization of V⁴⁺ ions in specific crystallographic sites in the structures, as expected from Robin and Day's mixed-valence compound classification (31).

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